IGBT - Shorted-Anode

1300 V, 30 A

FGH30S130P

Description

Using advanced field stop trench and shorted−anode technology, ON Semiconductor's shorted−anode trench IGBTs offer superior conduction and switching performances for soft switching applications. The device can operate in parallel configuration with exceptional avalanche capability. This device is designed for induction heating and microwave oven.

Features

- High Speed Switching
- Low Saturation Voltage: $V_{CE(sat)}$ =1.75 V @ I_C = 30 A
- High Input Impedance
- This Device is Pb−Free and is RoHS Compliant

Applications

- Induction Heating, Microwave Oven

ON Semiconductor®

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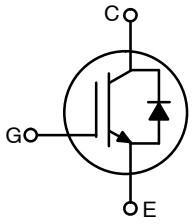
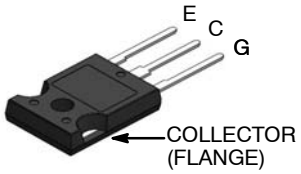
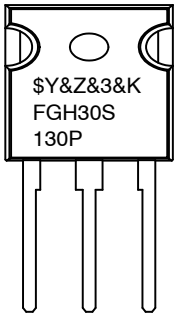




TO−247−3LD
CASE 340CK

MARKING DIAGRAM



$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FGH30S130P	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Description		Symbol	Rating	Unit
Collector to Emitter Voltage		V_{CES}	1300	V
Gate to Emitter Voltage		V_{GES}	±25	V
Collector Current	T_C = 25°C	I_C	60	A
Collector Current	T_C = 100°C		30	A
Pulsed Collector Current (Note 1)		I_{CM}	90	A
Diode Continuous Forward Current	T_C = 25°C	I_F	60	A
Diode Continuous Forward Current	T_C = 100°C		30	A
Maximum Power Dissipation	T_C = 25°C	P_D	500	W
Maximum Power Dissipation	T_C = 100°C		250	W
Operating Junction Temperature		T_J	−55 to +175	°C
Storage Temperature Range		T_{stg}	−55 to +175	°C
Maximum Lead Temp. for soldering Purposes, 1/8” from case for 5 seconds		T_L	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. Limited by Tjmax.

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case, Max	$R_{\theta JC}$(IGBT)	–	0.3	°C/W
Thermal Resistance, Junction to Ambient, Max	$R_{\theta JA}$	–	40	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Reel Size	Tape Width	Quantity
FGH30S130P	FGH30S130P	TO−247	–	–	30

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector Cut−Off Current	I_{CES}	V_{CE} = 1300, V_{GE} = 0 V	–	–	1	mA
G−E Leakage Current	I_{GES}	V_{GE} = V_{GES}, V_{CE} = 0 V	–	–	±500	nA
ON CHARACTERISTICs						
G−E Threshold Voltage	$V_{GE(th)}$	I_C = 30 mA, V_{CE} = V_{GE}	4.5	6.0	7.5	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 30 A, V_{GE} = 15 V, T_C = 25°C	–	1.75	2.3	V
		I_C = 30 A, V_{GE} = 15 V, T_C = 125°C	–	1.85	–	V
		I_C = 30 A, V_{GE} = 15 V, T_C = 175°C	–	1.9	–	V
Diode Forward Voltage	V_{FM}	I_F = 30 A, T_C = 25°C	–	1.7	2.2	V
		I_F = 30 A, T_C = 175°C	–	2.1	–	V

ELECTRICAL CHARACTERISTICS OF THE IGBT (T_C = 25°C unless otherwise noted) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ies}	V_{CE} = 30 V, V_{GE} = 0 V, f = 1 MHz	–	3345	–	pF
Output Capacitance	C_{oes}		–	75	–	pF
Reverse Transfer Capacitance	C_{res}		–	60	–	pF
SWITCHING CHARACTERISTICS						
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 600 V, I_C = 30 A, R_G = 10 Ω, V_{GE} = 15 V, Resistive Load, T_C = 25°C	–	39	–	ns
Rise Time	t_r		–	360	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	620	–	ns
Fall Time	t_f		–	160	210	ns
Turn−On Switching Loss	E_{on}		–	1.3	–	mJ
Turn−Off Switching Loss	E_{off}		–	1.22	1.6	mJ
Total Switching Loss	E_{ts}			2.52	–	mJ
Turn−On Delay Time	$t_{d(on)}$	V_{CC} = 600 V, I_C = 30 A, R_G = 10 Ω, V_{GE} = 15 V, Resistive Load, T_C = 175°C	–	38	–	ns
Rise Time	t_r		–	375	–	ns
Turn−Off Delay Time	$t_{d(off)}$		–	635	–	ns
Fall Time	t_f		–	270	–	ns
Turn−On Switching Loss	E_{on}		–	1.59	–	mJ
Turn−Off Switching Loss	E_{off}		–	1.78	–	mJ
Total Switching Loss	E_{ts}		–	3.37	–	mJ
Total Gate Charge	Q_g	V_{CE} = 600 V, I_C = 30 A, V_{GE} = 15 V	–	372.3	–	nC
Gate to Emitter Charge	Q_{ge}		–	18.7	–	nC
Gate to Collector Charge	Q_{gc}		–	156.2	–	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

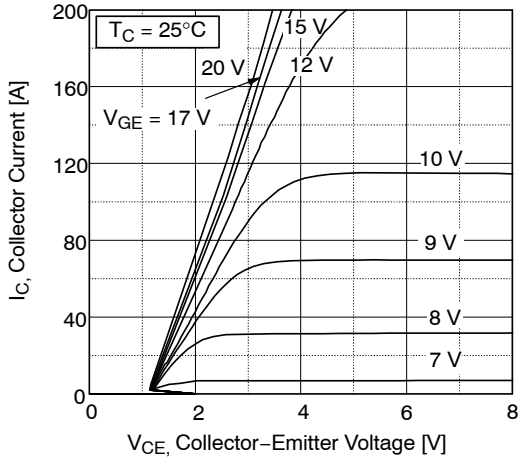


Figure 1. Typical Output Characteristics

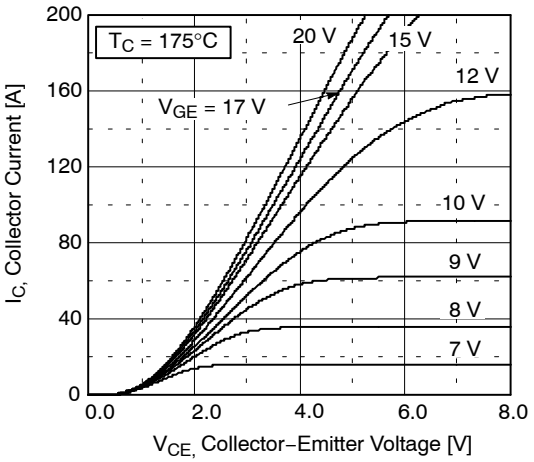


Figure 2. Typical Output Characteristics

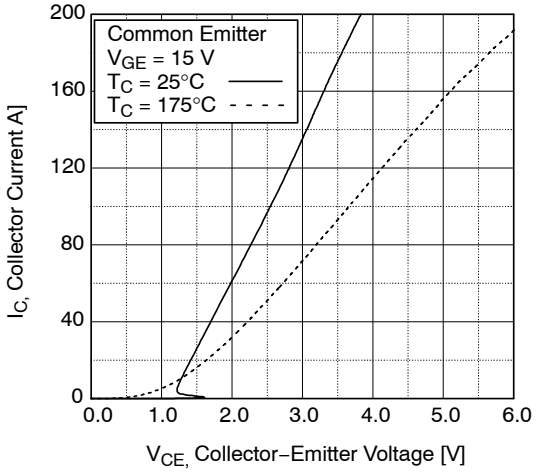


Figure 3. Typical Saturation Voltage Characteristics

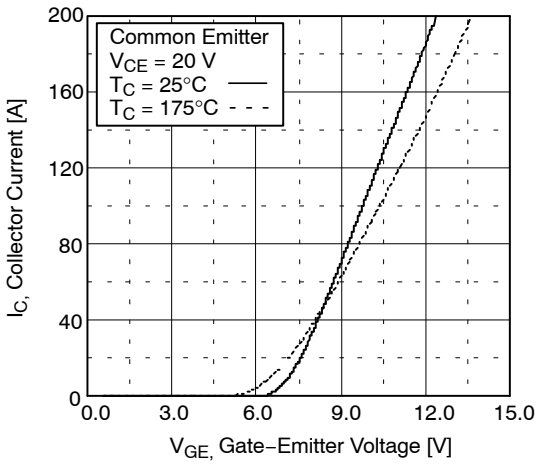


Figure 4. Transfer Characteristics

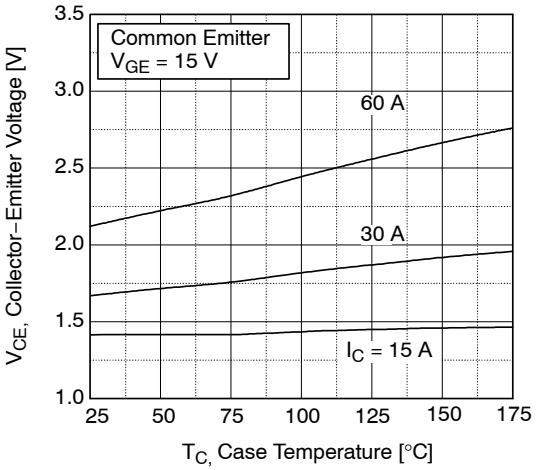


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

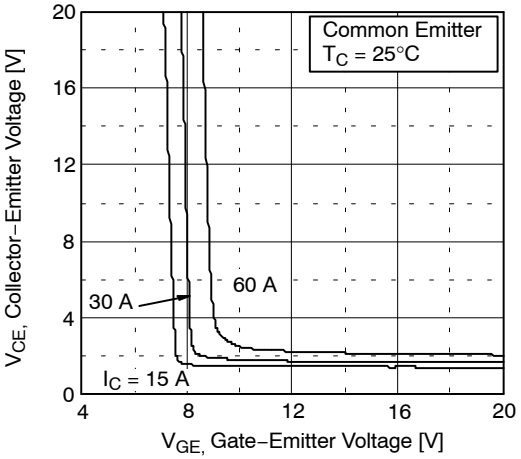


Figure 6. Saturation Voltage vs. V_{GE}

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

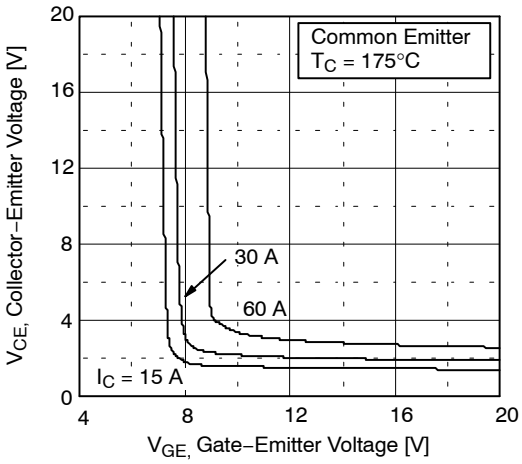


Figure 7. Saturation Voltage vs. V_{GE}

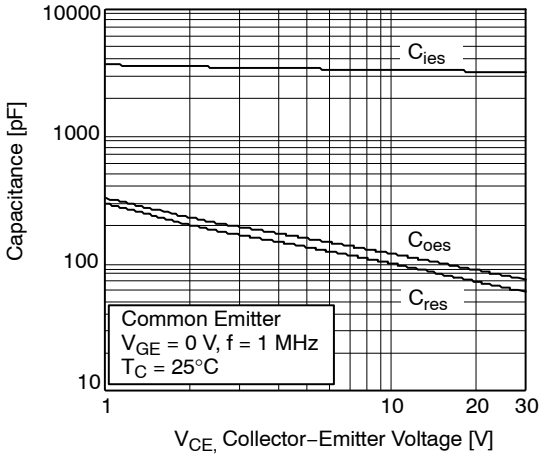


Figure 8. Capacitance Characteristic

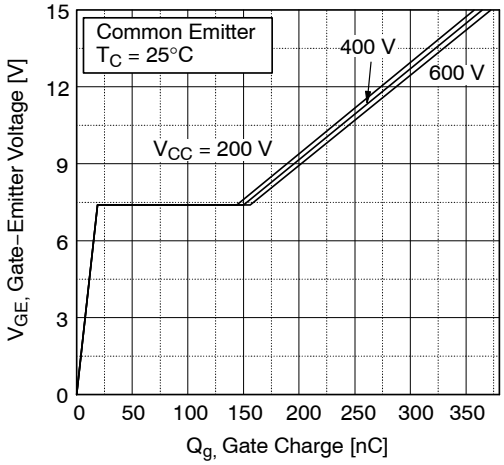


Figure 9. Gate Charge Characteristics

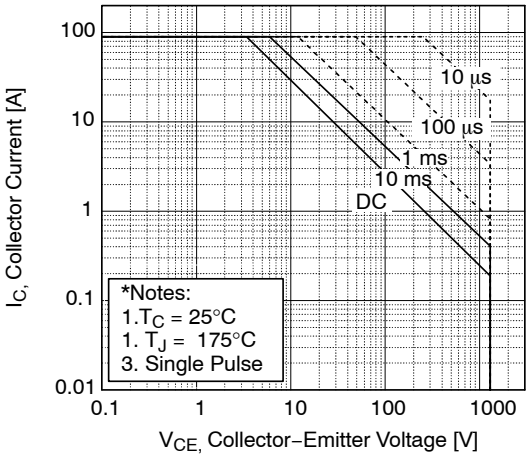


Figure 10. SOA Characteristics

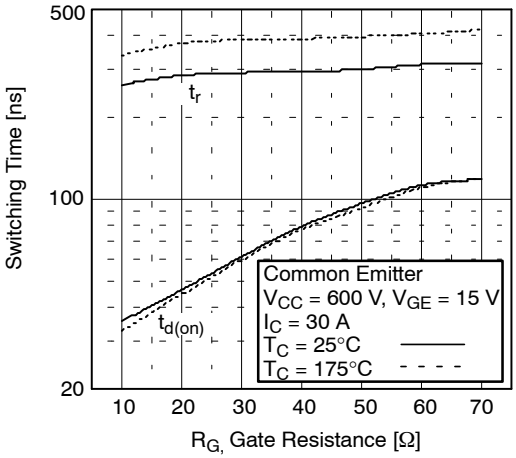


Figure 11. Turn−On Characteristics vs. Gate Resistance

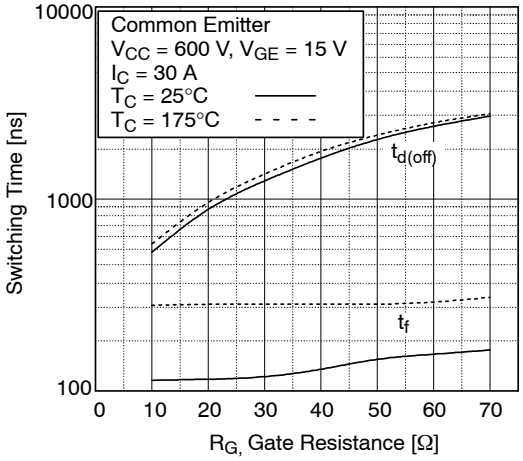


Figure 12. Turn−Off Characteristics vs. Gate Resistance

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

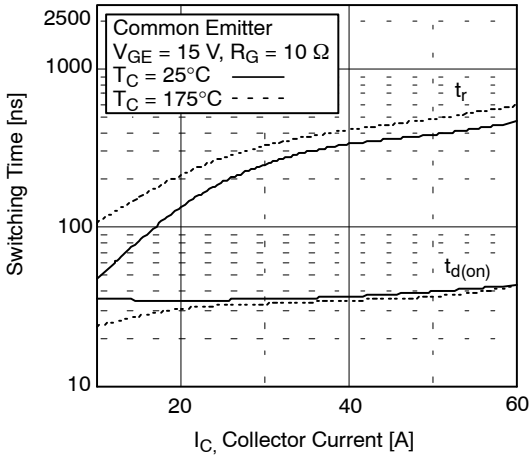


Figure 13. Turn−On Characteristics vs. Collector Current

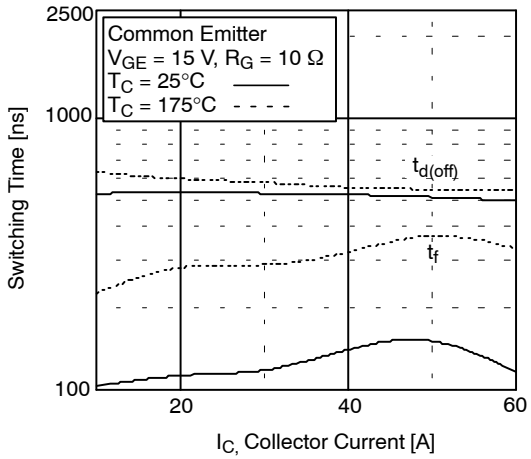


Figure 14. Turn−Off Characteristics vs. Collector Current

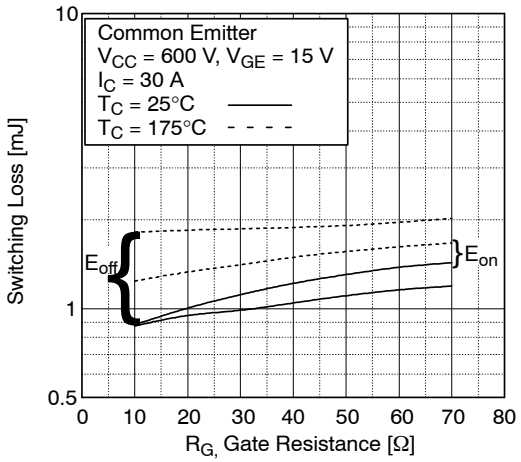


Figure 15. Switching Loss vs. Gate Resistance

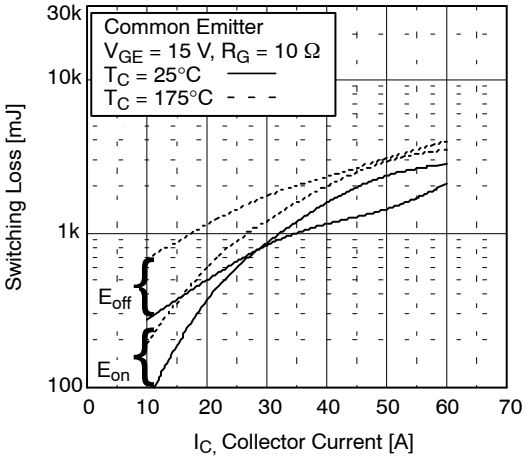


Figure 16. Switching Loss vs. Collector Current

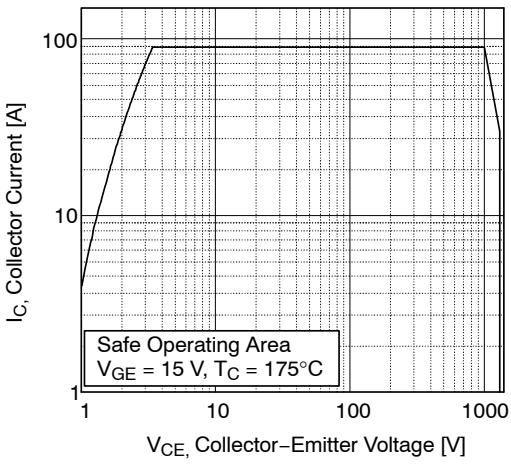


Figure 17. Turn−Off Switching SOA Characteristics

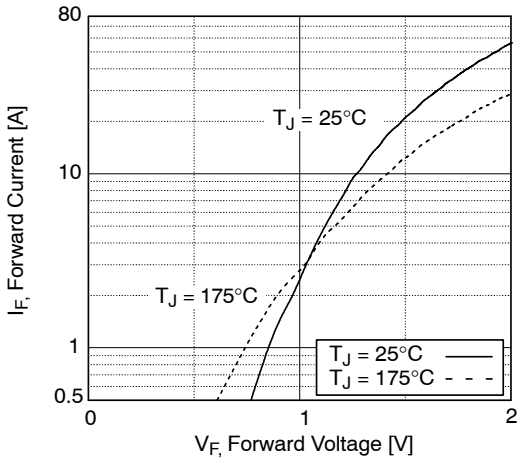


Figure 18. Forward Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

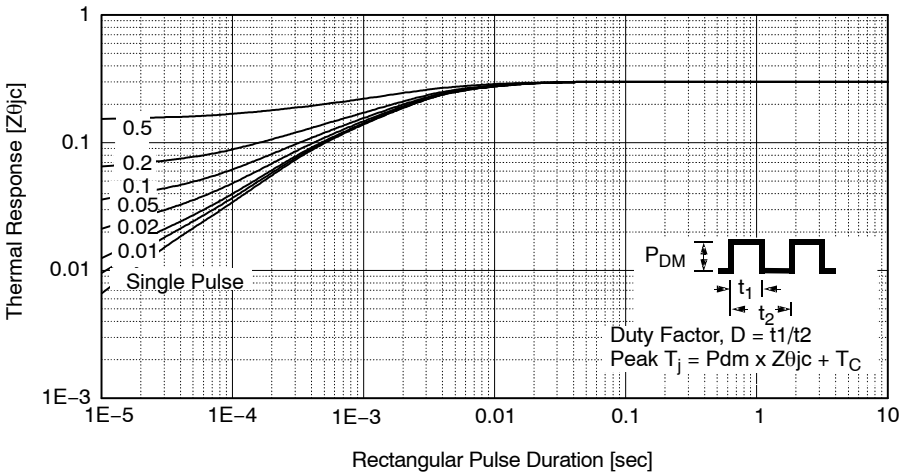


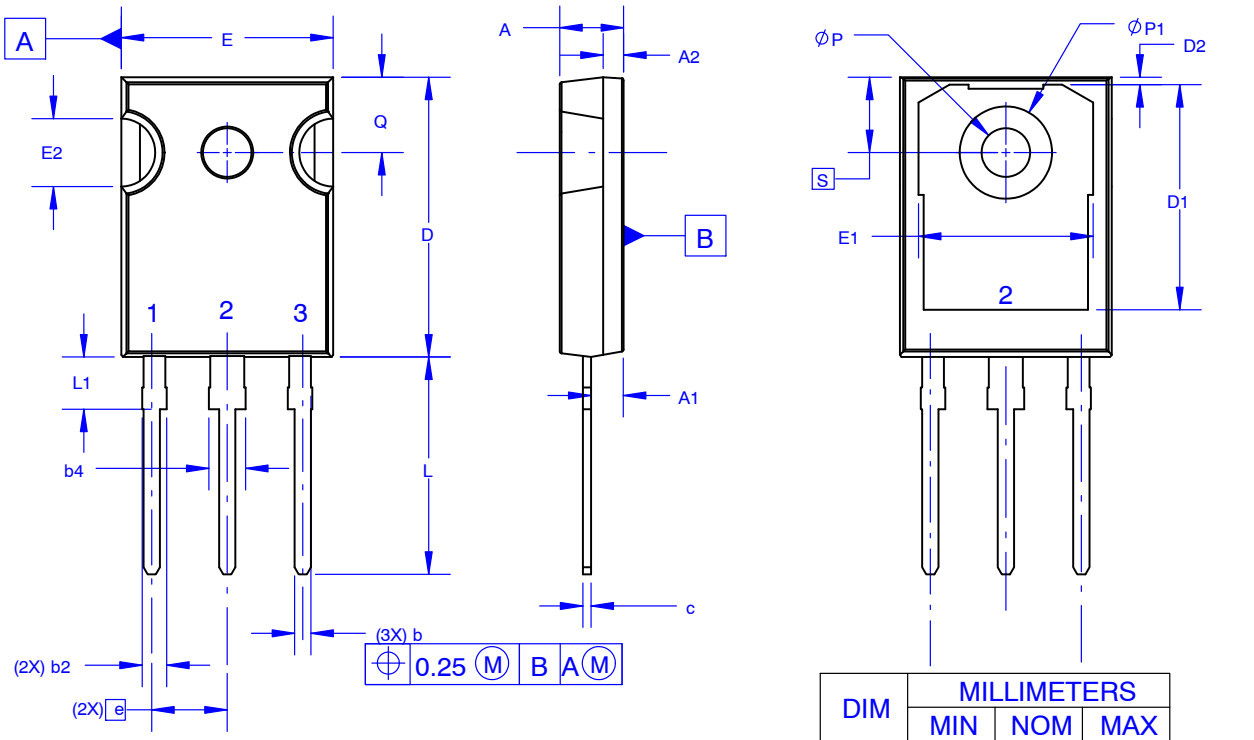
Figure 19. Transient Thermal Impedance of IGBT

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®

TO−247−3LD SHORT LEAD
CASE 340CK
ISSUE A

DATE 31 JAN 2019

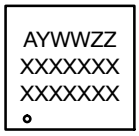


DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
ØP1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC
MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TO−247−3LD SHORT LEAD**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

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